



# S8550

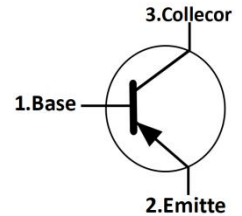
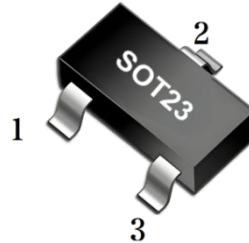
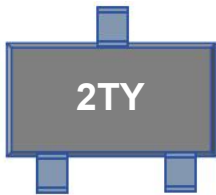
## PNP SILICON TRANSISTOR

### FEATURES

- \*Complementary to S8050
- \*Collector current:  $I_C=0.5A$

### MARKING

Type Code: Marking: 2TY



### ABSOLUTE MAXIMUM RATINGS (Tc=25°C, unless otherwise specified)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CB0</sub>	Collector-base voltage	-40	V
V <sub>CEO</sub>	Collector-emitter voltage	-25	V
V <sub>EBO</sub>	Emitter-base voltage	-5	V
I <sub>C</sub>	Collector current	-0.5	A
P <sub>C</sub>	Collector Power Dissipation	0.3	W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-60~150	°C
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	417	°C/W

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

### ELECTRICAL CHARACTERISTICS (Tc=25°C, unless otherwise specified)

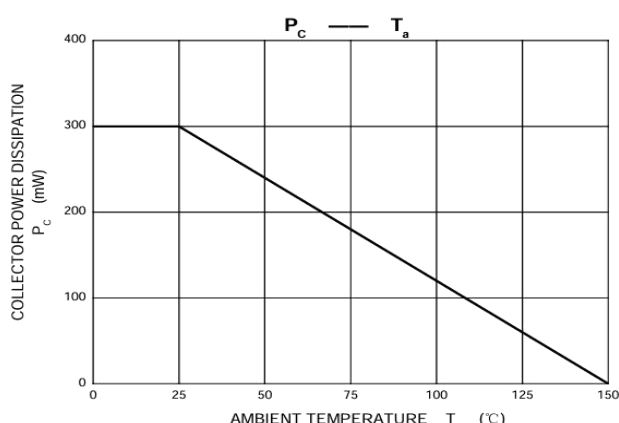
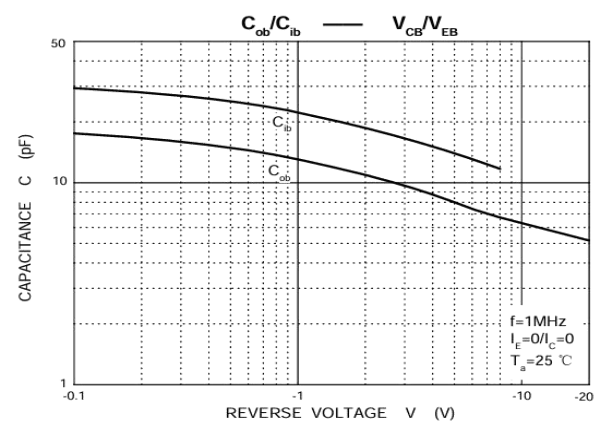
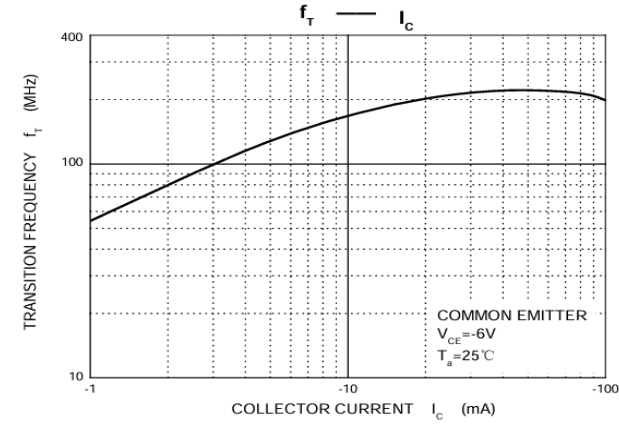
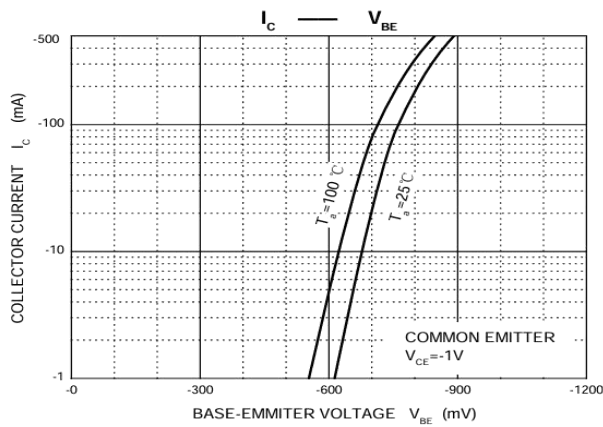
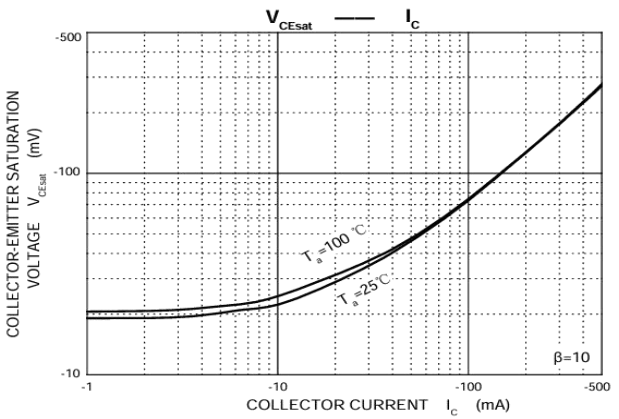
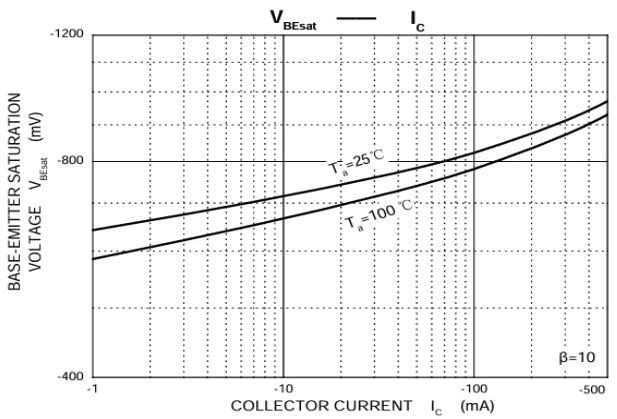
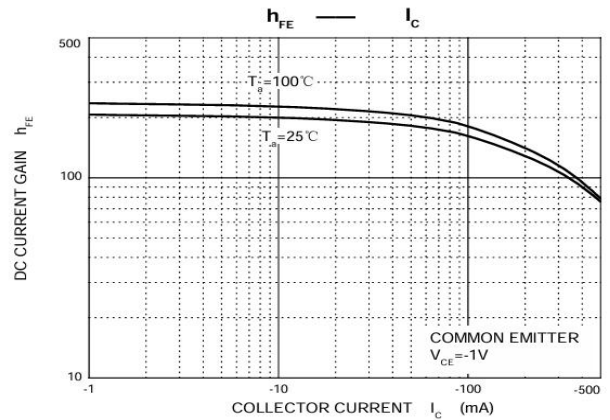
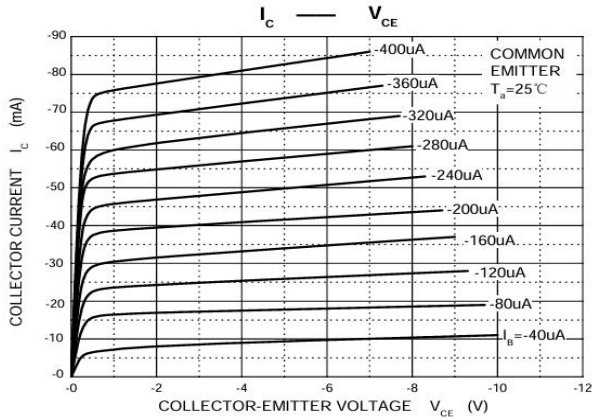
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-40		V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-25		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100μA, I <sub>C</sub> =0	-5		V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> =-40V, I <sub>E</sub> =0		-0.1	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =-20V, I <sub>B</sub> =0		-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0		-0.1	μA
DC Current Gain (CLASSIFICATION OF h <sub>FE1</sub> )	h <sub>FE1</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-50mA	A	120	200
			B	200	350
			C	300	400
	h <sub>FE2</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-500mA	50		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA		-0.6	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA		-1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-6V, I <sub>C</sub> =-20mA, f=30MHz	150		MHz



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## TYPICAL CHARACTERISTICS

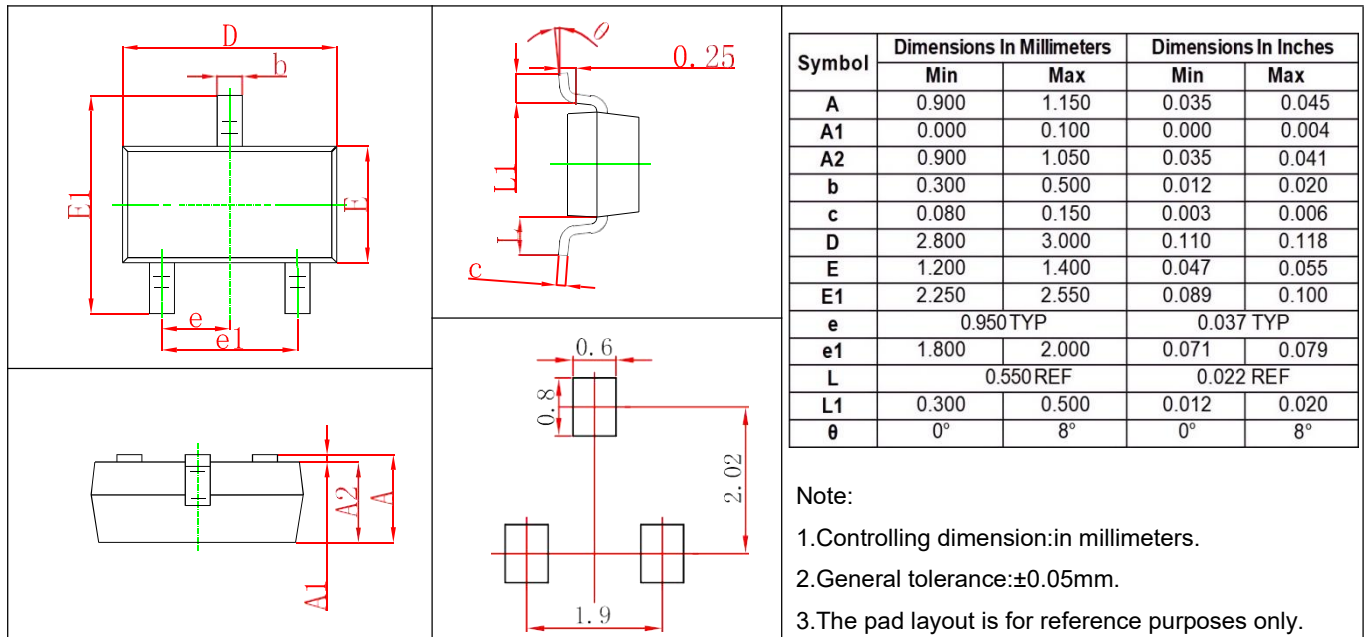




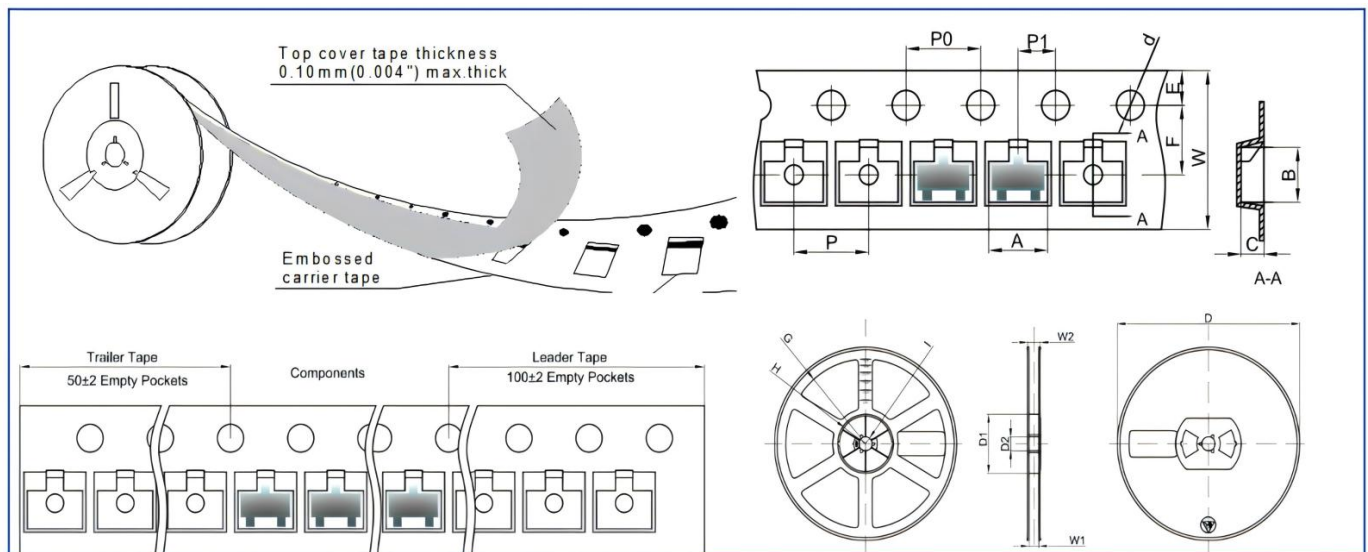
S8550

PNP SILICON TRANSISTOR

■ SOT23 PACKAGE OUTLINE DIMENSIONS



■ REEL PACKING



Dimensions are in millimeter										
PKG TYPE	A	B	C	d	E	F	Po	P	P1	W
SOT-23	3.15	2.77	1.22	Φ1.50	1.75	3.50	4.00	4.00	2.00	8.00
Reel Option	D	D1	D2	G	H	I	W1	W2	Q.TY PER REEL	
7" Dia	Φ178.0	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30	3000PCS	
13" Dia	Φ330.0	/	13.00	/	/	R6.50	9.50	12.30	10000PCS	